SENSITRON SEMICONDUCTOR

SHD120235 15LJQ150

TECHNICAL DATA DATA SHEET 4998, REV. -

HERMETIC SCHOTTKY RECTIFIER

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	150	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form (Single)	15	A
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave (per leg)	150	A
Maximum Thermal Resistance	$R_{ ext{ heta}JC}$	-	1.21	°C/W
Max. Junction Temperature	TJ	-	-65 to +200	°C
Max. Storage Temperature	T _{stg}	-	-65 to +200	°C

Electrical Characteristics

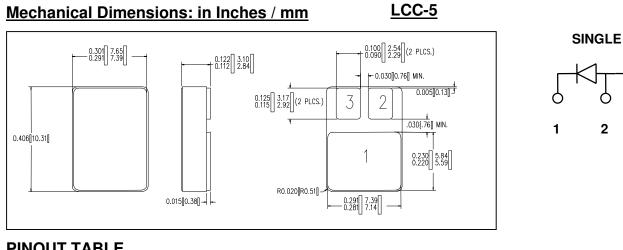
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.93	V
(per leg)	V _{F2}	@ 15A, Pulse, T _J = 125 °C	0.77	V
Max. Reverse Current	I _{R1}	@V _R = 150V, Pulse,	0.5	mA
		T _J = 25 °C		
(per leg)	I _{R2}	@V _R = 150V, Pulse,	8	mA
		T _J = 125 °C		
Max. Junction Capacitance	CT	@V _R = 5V, T _C = 25 °C	500	pF
(per leg)		f _{SIG} = 1MHz,		
		$V_{SIG} = 50 mV (p-p)$		

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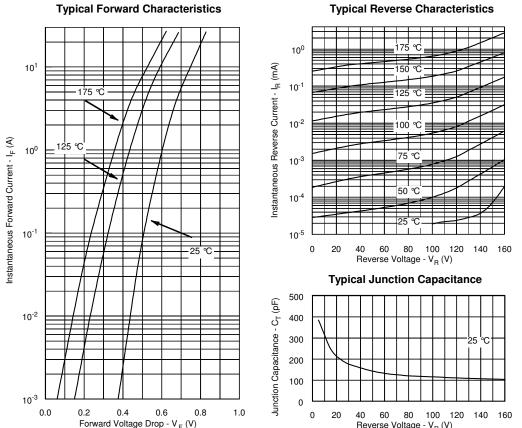
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PINOUT TABLE			
DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE

Note: The V_f curves shown are for the unpackaged die only.



Forward Voltage Drop - V_F (V) Reverse Voltage - V_R (V)

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TECHNICAL DATA

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